Atty. Dkt. No. 039153-0667

IE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Qi XIANG

Title:

STRAINED SILICON MOSFET HAVING

IMPROVED CARRIER MOBILITY, STRAINED SILICON CMOS DEVICE,

AND METHODS OF THEIR

**FORMATION** 

Appl. No.:

10/684,727

Filing Date:

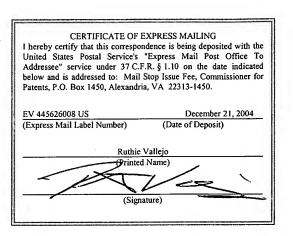
10/14/2003

Examiner:

T.Manh

Art Unit:

2822



## TRANSMITTAL OF FORMAL DRAWINGS

Mail Stop Issue Fee Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Transmitted herewith is the proposed drawing correction of Figures 1 and 2 (1 sheet) for the above-identified application. The Official Draftsperson is respectfully requested to approve these drawings for entry into the application.

Respectfully submitted,

Date 21 December 2004

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